AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Original) An electronic component comprising:

a conductive pattern provided on an insulating substrate;

a metal film formed by a plating method on a surface of the conductive pattern; and

a metal oxide layer formed by oxidizing the metal film and disposed on the surface of the conductive pattern.

2. (Currently amended) The electronic component as defined in claim 1, wherein the metal film is formed by a plating method on a surface of the conductive pattern and a space between a plurality of electrodes of the pattern on the substrate.

3. (Previously presented) The electronic component as defined in claim 1, wherein the metal film is formed by a plating method on a surface of the substrate, where the conductive pattern is provided.

4. (Previously presented) The electronic component as defined in claim 1, wherein the substrate uses a ceramic substrate.

5. (Previously presented) The electronic component as defined in claim 1, wherein the substrate uses a glass-ceramic substrate.

6. (Previously presented) The electronic component as defined in claim 1, wherein the substrate uses an organic substrate.

7. (Previously presented) The electronic component as defined in claim 1, wherein the conductive pattern uses electrode material including at least Ag.

8. (Original) The electronic component of claim 7, wherein the electrode material includes one material selected from the group consisting of Ag, Ag – Pt, and Ag – Pd.

9. (Previously presented) The electronic component as defined in claim 1, wherein the metal oxide layer includes one material selected from the group consisting of NiO, ZnO, and CuO.

10. (Previously presented) The electronic component as defined in claim 9, wherein the metal oxide layer has a thickness ranging from 0.5μm to 5μm.

11. (Cancelled)

12. (Currently amended) The electronic component as defined in claim 1, wherein a part of the conductive pattern is exposed outward from the surface of the component.

13. (Previously presented) The electronic component as defined in claim 2, wherein a part of the conductive pattern and a part of the substrate are exposed outward.

14. (Currently amended) The electronic component as defined in claim 3, wherein a part of the conductive pattern and a part of the substrate are exposed outward from the surface of the component.

15. (Previously presented) A method of manufacturing an electronic component, the method comprising the steps of:

forming a conductive pattern on an insulating substrate;

forming a metal film by a plating method on a surface of the conductive pattern; and

forming a metal oxide layer on the surface of the conductive pattern by oxidizing the metal film.

16. (Previously presented) The method of manufacturing an electronic component as defined in claim 15, wherein the method comprises the steps of:

forming the metal film by a plating method on a surface of the conductive pattern and on a space between electrodes of the pattern on the substrate.

17. (Previously presented) The method of manufacturing an electronic component as defined in claim 14, wherein the method comprises the steps of:

forming the metal film by a plating method on a surface of the substrate, where the conductive pattern is formed.

18. (Previously presented) The method as defined in one of claim 15, wherein the plating method uses an electroless plating method.

19. (Previously presented) The method as defined in claim 15 wherein the oxidizing is done by a heat treatment.

20. (Previously presented) The method as defined in claim 19, wherein the heat treatment is carried out at a temperature not higher than a melting point of the conductive pattern.

21. (Previously presented) A method of manufacturing an electronic component, the method comprising the steps of:

forming a conductive pattern on an insulating substrate;

forming a nickel film by a plating method at least on a surface of the conductive pattern;

forming nickel oxide as a metal oxide layer at least on the surface of the conductive pattern by providing the nickel film with an oxidation heat treatment at a temperature between 850℃ and a melting point of electrode material forming the conductive pattern.